Amendments to the Specification

Please amend the paragraph at page 21, lines 1-9 in the following manner:

A length L between the electrodes 2 and 3 may be in a range ~~of~~ from a few thousand Å ~~or~~ to a few ~~handred~~ hundred μm. Alternatively, considering a voltage or a like applied between the electrodes 2 and 3, the length may be in a range ~~of~~ from 1μm ~~or~~ to 100μm. Considering a resistance value and an electron emission characteristic of the electrodes 2 and 3, a width W of the electrodes 2 and 3 is in a range ~~of~~ from a few μm ~~or~~ to a few hundred μm and a thickness d of the electrodes 2 and 3 is in a range ~~of~~ from 100 Å ~~or~~ to 1μm.

Please amend the paragraph at page 21, line 10 through page 22, line 13 in the following manner:

A tabular surface conduction electron-emitting device manufacturing method will be described with reference to FIG.3A, FIG.3B, and FIG.3C. FIG.3A is a diagram showing a state of forming the electrodes 2 and 3 on the substrate 1, FIG.3B is a diagram showing a state of forming the conductive thin film 4 on the electrodes 2 and 3, and FIG.3C is a diagram showing a state of forming the electron emitting part 5 in the conductive thin film 4~~)~~. As the conductive thin film 4, in order to obtain a preferable electron emission characteristic, a micro-particle film configured of micro-particles may be used. The thickness of the ~~electrodes 2 and 3~~ conductive thin film 4 is selectively set based on a step-coverage to the electrodes 2 and 3, a resistance value between the electrodes 2 and 3, an electric forming condition that will be described later, and a like. The thickness may be in a range ~~of~~ from a few Å ~~or~~ to a few thousand Å. Preferably, the thickness is in a range ~~of~~ from 10Å ~~or~~ to 500Å. Moreover, the resistance value Rs of the micro-particle film may be the second power of 10 or the seventh power of 10Ω. The resistance value Rs is obtained by a formula R=Rs(1/w) where t denotes the thickness of the electrodes 2 and 3, w denotes the width of the electrodes 2 and 3, and the resistance R of the thin film at the length "1". Also, the resistance value Rs is expressed by Rs=ρ/t where ρ denotes a resistivity of the thin film material. In the embodiment, the electric process is illustrated as a forming process. However, the forming process is not limited to the electric process. Any method for forming a high resistance state

by causing a crack to the film can be applied.

Please amend the paragraph at page 22, line 23 through page 23, line 8 in the following manner:

The micro-particle film described in the embodiment represents a film as a set of a plurality of micro-particles. A microscopic configuration can show not only a state of a dispersion arrangement in that micro-particles are dispersed but also a state in that the micro-particles are adjacent each other or a state in that the micro-particles are overlapped each other (including a state in that some particles form a set like an island as a whole. A particle diameter of each micro-particle is in a range from a few Å ~~or~~ to 1μm. A suitable particle diameter may be in a range from 10Å ~~or~~ to 200μm.

Please amend the paragraph at page 94, lines 9-16 in the following manner:

FIG. 29A and FIG. 29B are diagrams showing a configuration of a fluorescent screen used in the image forming apparatus to which the present invention can be applied. In FIG. 29A, a fluorescent screen of a black ~~strap~~ stripe type is shown. In FIG. 29B, a fluorescent screen of the black matrix type is shown. In FIG. 29A and FIG. 29B, 91 denotes a black conductive member and 92 denotes a fluorescent material.

Please amend the paragraph at page 94, line 17 through page 95, line 5 in the following manner:

The fluorescent screen 84 is made up of only a fluorescent material in a case of monochrome. In a case of a color fluorescent screen, the fluorescent screen 84 is made up of a black conductive member 91 called a ~~blackstrap~~ black stripe or a black matrix. By providing the ~~blackstrap~~ black stripe or the black matrix, borders among fluorescent materials 92 of three primary colors become black in case of the color fluorescent screen, so that it is possible to suppress obviousness of a color mixture and to suppress deterioration of a contrast caused by an outer lit reflex by the fluorescent screen 84. As a material of the black ~~strap~~

stripe, a material including a black lead as a main composition is generally used. Alternatively, any material, which is conductive and have less optical transmission and reflex, can be applied.

Please amend the paragraph at page 95, lines 6-17 in the following manner:

In the present invention, in order to configure the image displaying apparatus, the ~~blackstrap~~ black stripe direction of the fluorescent material 92 or two directions being an orthogonal each other in the black matrix, and two directions of the electron emitting devices 74 being orthogonal each other are determined to be arranged in parallel. In addition, the fluorescent material 92 corresponds to each of the electron emitting devices 74. In the image displaying apparatus having this configuration, since directions of a matrix and the locations are corresponded to each other, the image displaying apparatus having a remarkable high image quality can be realized.